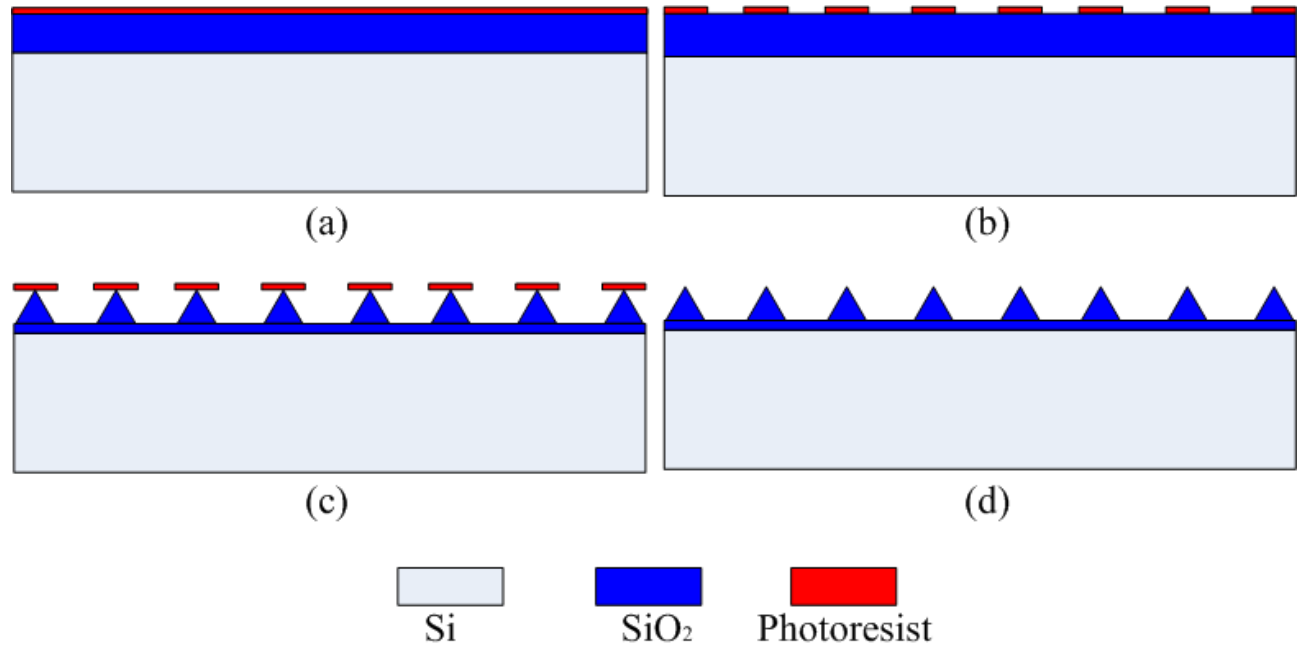


In the following figure we show the process sequence to obtain silicon oxide lines with triangular cross section in an attempt to fabricate a completely manufacturable template at wafer scale.



**Figure**

Fabrication process of the SiO<sub>2</sub> line arrays with peak structures: (a) Silicon wafers with 1 μm thickness of thermal SiO<sub>2</sub> were prepared and a photoresist layer was spin coated on the surface; (b) By means of optical lithography, the photoresist was patterned into arrays of lines with 1 μm periodicity; (c) The wafer was etched isotropically in diluted HF; (d) Photoresist was finally removed in acetone.